

ABSTRACT OF THE DISCLOSURE

A method of depositing an optical quality silica film on a substrate is described wherein the film is formed on the substrate by plasma enhanced chemical vapor deposition (PECVD) in the presence of reactive gases while controlling the total
5 pressure of the gases. The as-deposited film is then subjected to a low temperature treatment between 400° to 1200°C to minimize the presence of contaminant compounds in the film.